



ELECTRONICS, INC.
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1N4933 thru 1N4937 Silicon Rectifier General Purpose, Fast Recovery DO-41 Type Package

Features:

- Fast Switching for High Efficiency
- Low Forward Voltage Drop
- Low Leakage Current
- High Forward Surge Capability

Maximum Ratings and Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Maximum Repetitive Peak Reverse Voltage, V_{RRM}	
1N4933	50V
1N4934	100V
1N4935	200V
1N4936	400V
1N4937	600V
Maximum RMS Voltage, V_{RMS}	
1N4933	35V
1N4934	70V
1N4935	145V
1N4936	280V
1N4937	420V
Maximum DC Blocking Voltage, V_{DC}	
1N4933	50V
1N4934	100V
1N4935	200V
1N4936	400V
1N4937	600V
Maximum Average Forward Rectified Current, $I_{F(AV)}$	
.375" (9.5mm) Lead Length at $T_A = +75^\circ\text{C}$	1A
Peak Forward Surge Current, I_{FSM}	
8.3ms Single Half Sine-Wave Superimposed on Rated Load	30A
Maximum Reverse Recovery Current, I_{RM}	
.....	2A
Maximum Instantaneous Forward Voltage at 1A DC, V_F	
.....	1.2V

Maximum Ratings and Electrical Characteristics (Cont'd): ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Maximum DC Reverse Current at Rated DC Blocking Voltage, I_R

$T_A = +25^\circ\text{C}$	5 μA
$T_A = +100^\circ\text{C}$	100 μA

Maximum Reverse Recovery Time ($I_F = 1\text{A}$, $V_R = 30\text{V}$, $di/dt = 50\text{A}/\mu\text{s}$, $I_{rr} = 10\% I_{RM}$), t_{rr} ... 200ns

Typical Junction Capacitance (4V, 1MHz), C_J 12pF

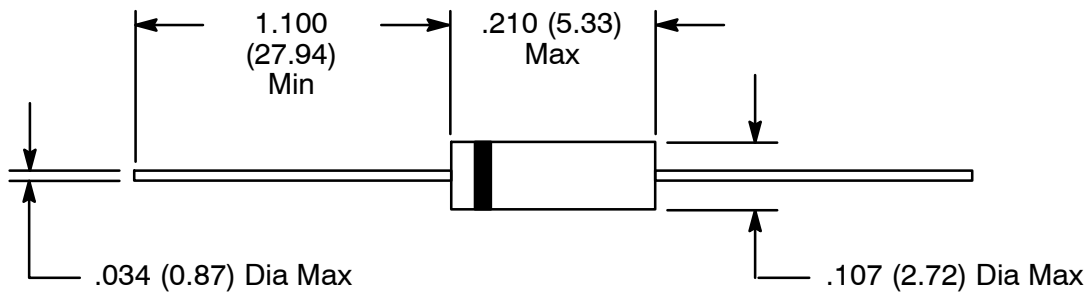
Operating Junction Temperature Range, T_J -50° to $+150^\circ\text{C}$

Storage Temperature Range, T_{stg} -50° to $+150^\circ\text{C}$

Typical Thermal Resistance, Junction-to-Ambient (Note 1), R_{thJA} $+55^\circ\text{C}/\text{W}$

Typical Thermal Resistance, Junction-to-Lead (Note 1), R_{thJL} $+25^\circ\text{C}/\text{W}$

Note 1. Measured at .375" (9.5mm) lead length, PCB mounted.



Color Band Denotes Cathode